

# **VDIC NOR Flash Memory**

## **VDRF64M16XS54XX1V90 USER MANUAL**

**Version : B0**

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# VDIC-Nor Flash Memory

**HIGH SPEED 3.0V 4M×16bit**

## 1 Description

The VDRF64M16XS54XX1V90 is a 64Mbit high-density simultaneous Read/Write non-volatile FLASH Memory module organized as 4M × 16bit.

Using high-performance and high – reliability technology chips, stacking with the well-known ORBITA Proprietary technology, this FLASH memory module provides a cost-effective solution for low power and high-capacity non-volatile memory data storage needs.

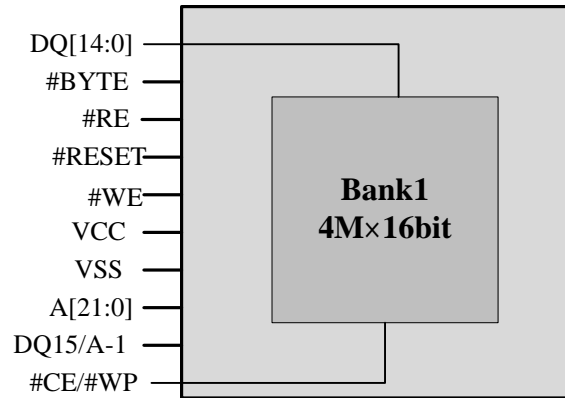
Each device of the module is a 64Mbit non-volatile FLASH Memory, organized 4M × 16bit that can be accessed by activating the associated control signals(#CE and #WP/ACC),and electrically erasable, read/write non-volatile flash memory. Any word can be programmed typically in 8μs. The device features 3.3V voltage read and write operation, with access times as fast as 90ns to eliminate the need for WAIT states in high-performance microprocessor systems. This device is designed to allow either single Sector or full Chip erase operation, where each Sector can be individually protected against program/erase operations or temporarily unprotected to erase or program. The device can sustain a minimum of 100K program/erase cycles on each Sector.

The VDRF64M16XS54XX1V90 module is packaged in a 54 sop package and is available for commercial, industrial and military temperature range.

## 2 Features

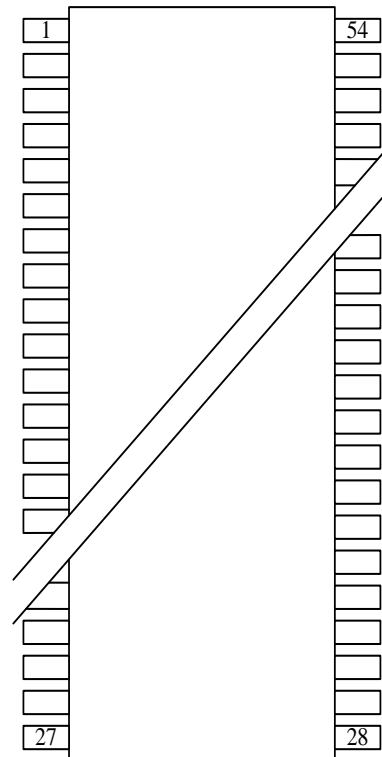
- Single power supply operation
  - Full voltage range: 2.7 to 3.6 volts read and write operations
- High performance
  - Access times as fast as 90 ns
- Low power consumption (typical values at 5MHz)
  - 9 mA typical active read current
  - 20 mA typical program/erase current
  - Less than 1  $\mu$ A current in standby or automatic sleep mode
- Flexible Sector Architecture:
  - Eight 8-Kbyte sectors, One hundred and twenty-seven 32K-Word / 64K-byte sectors
  - 8-Kbyte sectors for Top or Bottom boot
  - Sector/Sector Group protection: Hardware locking of sectors to prevent program or erase operations within individual sectors. Additionally, temporary Sector Group Unprotect allows code changes in previously locked sectors
- High performance program/erase speed
  - Word program time: 8 $\mu$ s typical
  - Sector erase time: 500ms typical
  - Chip erase time: 64s typical
- JEDEC Standard compatible
- Standard DATA# polling and toggle bits feature
- Unlock Bypass Program command supported
- Erase Suspend / Resume modes:
  - Read and program another Sector during Erase Suspend Mode
- Support JEDEC Common Flash Interface(CFI)
- Low Vcc write inhibit < 2.5V
- Minimum 100K program/erase endurance cycles
- #RESET hardware reset pin
  - Hardware method to reset the device to read mode
- #WP/ACC input pin
  - Write Protect (#WP) function allows protection of outermost two boot sectors, regardless of sector protect status
  - Acceleration (ACC) function provides accelerated program times
- Package Options
  - 54-pin SOP (Type 1)

### 3 BLOCK DIAGRAM



### 4 PIN DESCRIPTIONS

Pin Id	Pin #	Pin Id
NC	1	54
NC	2	53
A15	3	52
A14	4	51
A13	5	50
A12	6	49
A11	7	48
A10	8	47
A9	9	46
A8	10	45
A19	11	44
A20	12	43
#WE	13	42
#RESET	14	41
A21	15	40
#WP/ACC	16	39
RY/#BY	17	38
A18	18	37
A17	19	36
A7	20	35
A6	21	34
A5	22	33
A4	23	32
A3	24	31
A2	25	30
A1	26	29
NC	27	28



Pin Name	Function
A0-A21	22 Address inputs
DQ0-DQ14	15 Data Inputs/Outputs
DQ15/A-1	DQ15 (data input/output, in word mode), A-1 (LSB address input, in byte mode)
#CE	Chip Enable
#OE	Output Enable
#WE	Write Enable
#WP/ACC	Write Protect / Acceleration Pin
#RESET	Hardware Reset Pin
#BYTE	Byte/Word mode selection
RY/#BY	Ready/Busy Output
V <sub>cc</sub>	Supply Voltage(2.7-3.6V)
V <sub>ss</sub>	Ground
NC	Not Connected to anything

## 5 ELECTRICAL SPECIFICATIONS

### 5.1 ABSOLUTE MAXIMUM RATINGS

Characteristics	Symbol	Maximum ratings	Unit
Voltage on VCC supply relative to V <sub>ss</sub>	V <sub>CC</sub>	-0.5 to +4.0	V
Voltage on any pin relative to V <sub>ss</sub>	V <sub>IN</sub>	-0.5 to V <sub>CC</sub> +0.5	V
Power Dissipation	P <sub>D</sub>	1.0	W
Operating Temperature Range	T <sub>OPR</sub>	-55 ~ +125	°C
Storage Temperature Range	T <sub>STG</sub>	-65 to +150	°C

### 5.2 RECOMMENDED OPERATING RANGES

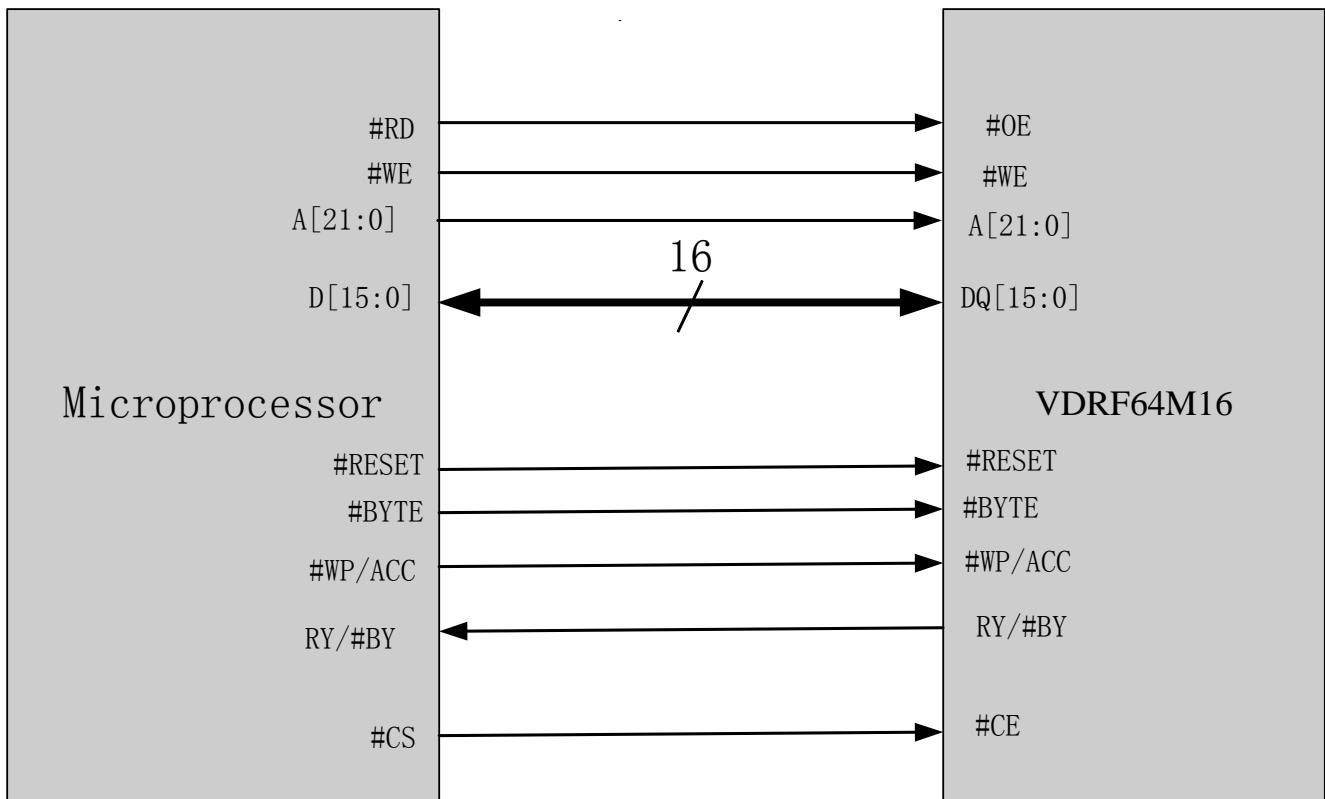
Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V <sub>CC</sub>	2.7	3.0	3.6	V
Input high voltage	V <sub>IH</sub>	2.1	—	V <sub>CC</sub> +0.3	V

Parameter	Symbol	Min	Typ	Max	Unit
Input low voltage	V <sub>IL</sub>	-0.5	—	0.8	V

5.3 DC Characteristics

Parameter	Symbol	Test Conditions	Min	Max	Unit
Output voltage low level	V <sub>OL</sub>	V <sub>CC</sub> =2.7V , I <sub>OL</sub> =+4mA	—	0.45	V
Output voltage high level	V <sub>OH</sub>	V <sub>CC</sub> =2.7V , I <sub>OH</sub> =-2mA	2.6	—	V

6 TYPICAL APPLICATION



## 7 ORDERING INFORMATION

1	2	3	4	5	6	7	8	9	10	11	12	13
<u>VD</u>	<u>RF</u>	<u>64M</u>	<u>16</u>	<u>V</u>	<u>S</u>	<u>54</u>	<u>E</u>	<u>E</u>	<u>1</u>	<u>V</u>	<u>90</u>	-
VDIC												
NOR FLASH												
Capability: 64M bit												
Bus Width: 16bit												
R= Radiation Data Tested; V= Generic Radiation Data Available												
Package: S=SOP												
54=54 Pin												
Temperature::E=0~70°C;I=-40~85°C;M=-55~125°C; S=Specific												
Quality: E= Sample; B= Industry; M=Military; S= Space												
Stacking Layer:1=1layer												
Power Supply :V=3.0V												
Speed:90= 90ns												
-I、 -K or blank space=First Version												

Part Number	Capacity (bit)	Bus Width (bit)	Radiation			Packaging	Temperature ( °C )
			TID <sup>1</sup>	SEL <sup>2</sup>	SEU <sup>3</sup>		
VDRF64M16VS54EE1V90	64M	16	-	-	-	SOP54	0 ~ + 70
VDRF64M16VS54IB1V90	64M	16	-	-	-	SOP54	-40 ~ + 85
VDRF64M16VS54MB1V90	64M	16	-	-	-	SOP54	-55 ~ + 125
VDRF64M16VS54MM1V90	64M	16	-	-	-	SOP54	-55 ~ + 125
VDRF64M16RS54MS1V90	64M	16	> 15	> 47.5	> 10	SOP54	-55 ~ + 125

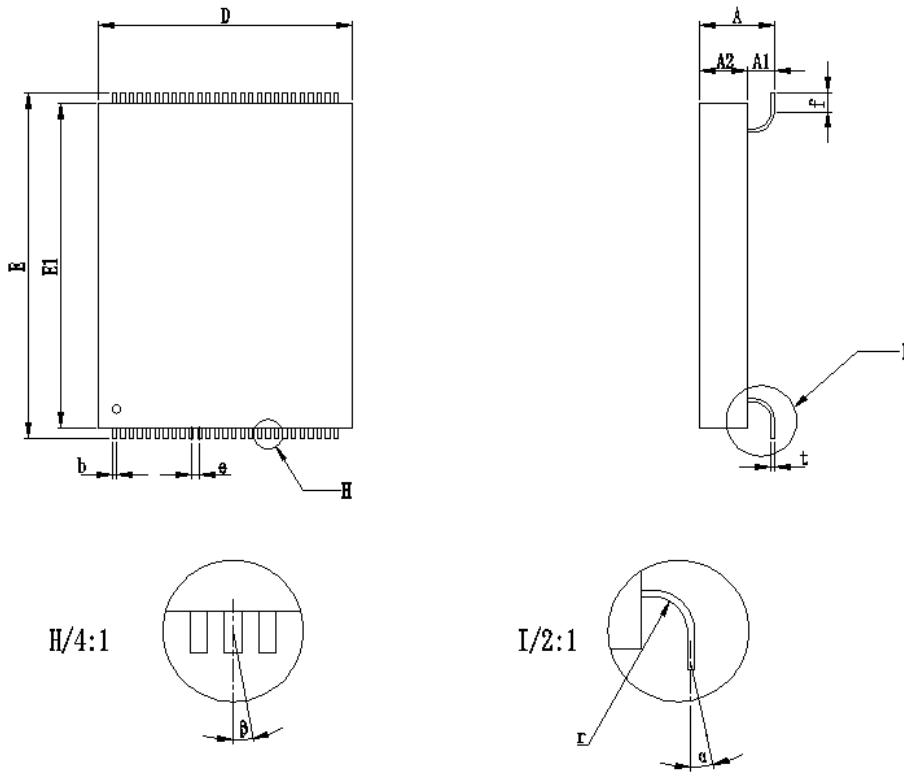
<sup>1</sup> TID: Total Dose (Krad(Si))

<sup>2</sup> SEL: LET Threshold (Mev.cm<sup>2</sup>/mg)

<sup>3</sup> SEU:SEU Threshold (Mev.cm<sup>2</sup>/mg)



### 8 PACKAGE DIMENSIONS



	Min	Max
A	3.70	4.40
A2	2.50	3.10
D	14.40	14.80
E	19.80	20.2
E1	18.80	19.20
f	1.20	
b	0.25	
e	0.50	
r	1.00	
t	0.20	
$\alpha$	$\leq 3^\circ$	
$\beta$	$\leq 3^\circ$	

NOTE : 1. Unit : mm

2. A1= A - A2

## 9 REVISION HISTORY

Revision	Date	Description of Change
A0	Nov 3,2015	First Created
A1	Mar 14,2016	Modified PIN DESCRIPTIONS
A2	Aug 23,2016	Modified ORDERING INFORMATION
A3	Jan 9,2017	Modified the Truth Table
A4	Oct.25,2017	Changed company's name to Zhuhai Orbita Aerospace Science & Technology Co., Ltd
A5	Nov 10,2017	Add or reduce chapters
B0	Mar 6,2018	Modified DC characteristics table